

REMARKS

The specification has been amended to correct the identity of Figures 2a-2d, 3a-3b, 6a-6c, 7a-7b, 8a-8b, 9a-9b, 10a-10c and 11a-11b. Claims 15 and 23 have been amended to delete multiple-dependency and claims 24-30 have been added accordingly.

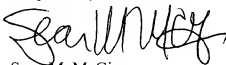
Attached hereto is a marked-up version of the changes made to the claims by the current preliminary amendment. The attached pages are captioned "**Version with markings to show changes made.**"

Early, favorable prosecution on the merits is respectfully requested.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's

Deposit Account No. 50-0481.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the specification:

Figures 2a-2d show[s] one example of the method of the present invention for producing a semiconductor device.

Figures 3a-3b show[s] another example of the method of the present invention for producing a semiconductor device.

Figures 6a-6c show[s] another example of the conventional method for producing a semiconductor device.

Figures 7a-7b show[s] another example of the conventional method for producing a semiconductor device.

Figures 8a-8b show[s] still another example of the conventional method for producing a semiconductor device.

Figures 9a-9b show[s] still another example of the conventional method for producing a semiconductor device.

Figures 10a-10c show[s] still another example of the conventional method for producing a semiconductor device.

Figures 11a-11b show[s] still another example of the method of the present invention for producing a semiconductor device.

In the claims:

15. (Amended) The method of forming a multi-layered insulation film according to [any one of claims 9 to 12] claim 9, characterized in that said semiconductor wafer is spin-coated with a solution containing said organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more, and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

23. (Amended) The method of producing a semiconductor device according to [any one of claims 16 to 20] claim 16, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.